

P

PATENT NUMBER
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10099963	03/19/2002	438	149	2823	<i>Long Pham</i>

****APPLICANTS:** Miyasaka Mitsutoshi;

****CONTINUING DATA VERIFIED:**
THIS APPLICATION IS A DIV OF 09/400,303 09/21/1999
WHICH IS A DIV OF 08/776,545 01/31/1997 PAT 6,066,516 *Long Pham*

FOREIGN APPLICATIONS VERIFIED:
JAPAN 7-159147 06/26/1995
JAPAN 8-161280 06/21/1996

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no 35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no Verified and Acknowledged Examiners's initials		ATTORNEY DOCKET NO. 038839.02
TITLE: Method for forming crystalline semiconductor layers, a method for fabricating thin film transistors, and a method for fabricating solar cells and active matrix liquid crystal devices U.S. DEPT. OF COMM./PAT. & TM-PTO-436L (Rev. 12-94)		

NOTICE OF ALLOWANCE MAILED		CLAIMS	
		Total Claims	0.0
ISSUE FEE		DRAWING	
Amount Due	Date Paid	Sheet Draw.	Fig. Draw.
<input type="checkbox"/> TERMINAL DISCLAIMER		Application Examiner	
		PREPARED FOR ISSUE	
WARNING: The information disclosed herein may be restricted. Unauthorized disclosure may be prohibited by the United States Code Title 35, Sections 122, 181 and 368. Possession outside the U.S. Patent & Trademark Office is restricted to authorized employees and contractors only.			

FILED WITH:

☐ DISK (CRF)

☐ CD-ROM

(Attached in pocket on right inside flap)